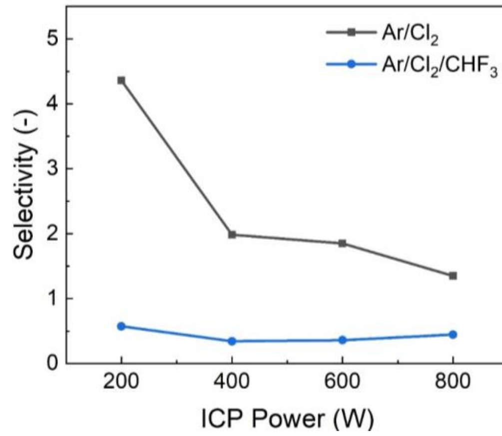


FIG. 1. Selectivity for dry etching of $SiO_2$ over AlN as a function of ICP power at a fixed RF power of 50 W.

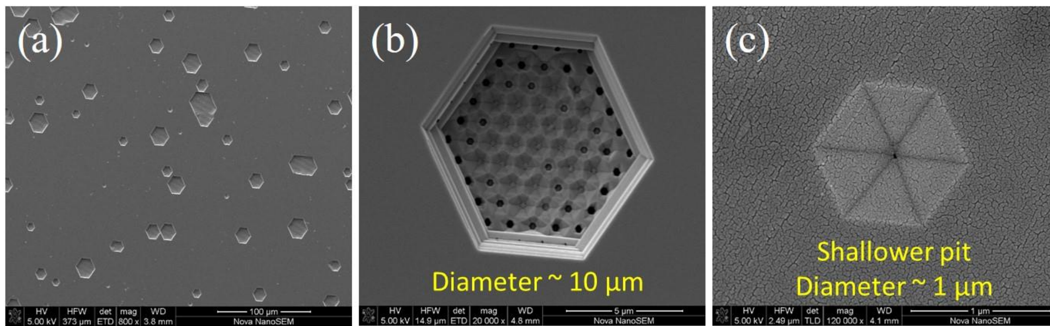


FIG. 2. SEM images of AlN surface after etching in KOH at 80℃. (a) pits formed on the surface (b) magnified view of large deep pit and (c) shallow, smaller pits

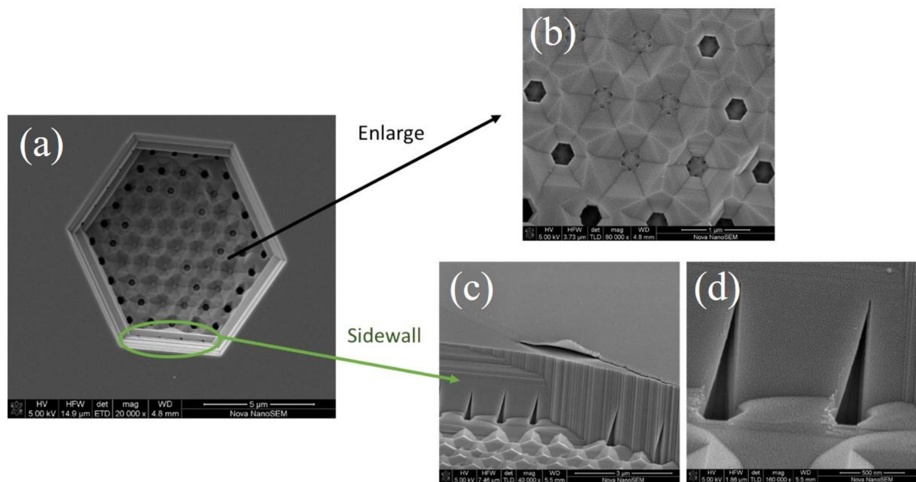


FIG. 3. SEM images of the bottom of one of the larger pits, showing (a) the exposed buffer layer, (b) the small hexagonal pits formed in that with the sapphire underneath, and (c)(d) the more detailed images of the sidewall of the etched large pit.